

Title (en)

FORMULATIONS COMPRISING AMMONIACAL HYDROXO-ZINC COMPOUNDS

Title (de)

FORMULIERUNGEN ENTHALTEND AMMONIAKALISCHE HYDROXO-ZINK-VERBINDUNGEN

Title (fr)

FORMULATION CONTENANT DES COMPOSÉS AMMONIACAUX D'HYDROXO-ZINC

Publication

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Application

EP 13712255 A 20130326

Priority

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- EP 2013056341 W 20130326

Abstract (en)

[origin: WO2013156274A1] The invention relates to ammoniacal formulations comprising a) at least one hydroxo-zinc compound and b) at least one compound of an element of the 3rd primary group, to the use thereof, to a method using said formulations to produce layers comprising ZnO and to electronic components produced using same.

IPC 8 full level

H01L 21/36 (2006.01)

CPC (source: CN EP RU US)

C01C 1/00 (2013.01 - RU); **C01G 9/02** (2013.01 - RU); **C23C 18/1216** (2013.01 - RU); **H01B 1/06** (2013.01 - EP US); **H01B 1/22** (2013.01 - EP US); **H01L 21/02554** (2013.01 - CN EP RU US); **H01L 21/02565** (2013.01 - CN EP RU US); **H01L 21/02628** (2013.01 - CN EP RU US); **H01L 21/34** (2013.01 - RU); **H01L 29/24** (2013.01 - US); **H01L 29/7869** (2013.01 - US)

Citation (search report)

See references of WO 2013156274A1

Citation (examination)

- JAECHUL PARK ET AL: "Source/Drain Series-Resistance Effects in Amorphous Gallium-Indium Zinc-Oxide Thin Film Transistors", IEEE ELECTRON DEVICE LETTERS, IEEE SERVICE CENTER, NEW YORK, NY, US, vol. 29, no. 8, 1 August 2008 (2008-08-01), pages 879 - 881, XP011231703, ISSN: 0741-3106, DOI: 10.1109/LED.2008.2000815
- TAEHWAN JUN ET AL: "Bias stress stable aqueous solution derived Y-doped ZnO thin film transistors", JOURNAL OF MATERIALS CHEMISTRY, ROYAL SOCIETY OF CHEMISTRY, GB, vol. 21, no. 35, 1 January 2011 (2011-01-01), pages 13524 - 13529, XP009189134, ISSN: 0959-9428, DOI: 10.1039/C1JM11586C

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